FORM: PTO-1449 (REV: 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	Atty Docket No: 98-1191.01	Serial No:	S. S
INFORMATION DI	SCLOSURE STATEMENT BY APPLICANT	Applicant: Gurtej S. Sandhu		S. P.
(37 CFR 1.98(b))	(use several sheets if necessary)	Filing Date: November 9, 2001	Group:	200

U.S. PATENT DOCUMENTS

Examiner		Document				
Initial		Number	Date	Name	Class	Subclass
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S. M. AM	EP 0 875 929 A2	11/04/98	Europe		 	 	
AN				H01L 21	768		
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Initial	1	OTHER ART (including author, title, date, pertinent pages, etc.)
L.J.M.E,	AR	Sabine Penka, et al., Integration Aspects of Flowfill and Spin-on-Glass Process for Sub-0.35 µm Interconnects, PROCEEDINGS OF THE IEEE 1998 INTERNATIONAL INTERCONNECT TECHNOLOGY CONFERENCE, at 271-273 (1998).
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Lynette J. Umg Eunini	Date Considered: 11/2-4-12 006-1
3	1/2/200 /

EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.

FORM: PT				IENT OF COMMERCE	Atty Docket No:	Serial No:	
(REV: 7-8	•			TRADEMARK OFFICE	98-1191.01 Applicant:		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Gurtej S. Sandhu Filing Date: Group:			
(37 CFR 1.9	8(b))		(use several	sheets if necessary)	Concurrently Herewit	ih	
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Initial			ОТІ	HER ART (including author	. title, date, pertinent page	s etc.)	
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L.T.ME,	AR	A. Hass Bar-llan, et al., A Comparative Study of Sub-micron Gap Filling and Planarization Techniques, PROCEEDINGS OF THE SPIE – THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING, at 277-288 (1995).					
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Z.J.NZ.	AS	Cal	lifornia, pp. 19	90			
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Examiner:	gnet	te T. W	ma-Er	Date Consi	dered: 12004	·	
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